

Features

- $V_{DS} = 100V, I_D = 17A$
 $R_{DS(ON)} < 70m\Omega @ V_{GS} = 10V$ (Typ:56m Ω)
 $R_{DS(ON)} < 85m\Omega @ V_{GS} = 4.5V$ (Typ:65m Ω)
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Mechanical Data

Case : Molded plastic body

Terminals : Solder plated, solderable per MIL-STD-750, Method 2026

Polarity : As marked

Mounting Position : Any

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

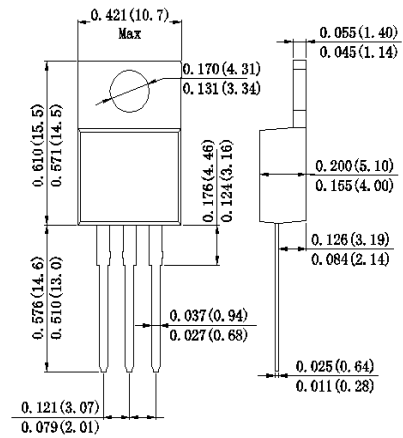
Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	17	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	12	A
Pulsed Drain Current	I_{DM}	60	A
Maximum Power Dissipation	P_D	55	W
Single pulse avalanche energy ^(Note 5)	E_{AS}	250	mJ
Drain Source voltage slope, $V_{DS} \leq 80V$,	dv/dt	50	V/ns
Drain Source voltage slope, $V_{DS} \leq 80V, I_{SD} < I_D$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

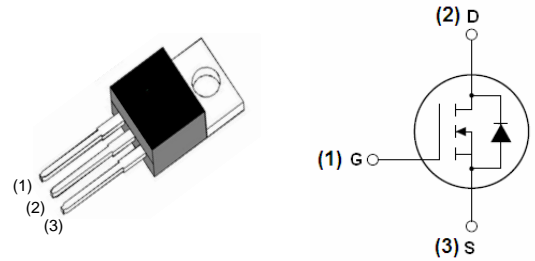
TO-220AB

RoHS
COMPLIANT

Pb-Free



Note: Dimensions in inches and (millimeters)



Schematic diagram

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.27	$^{\circ}\text{C}/\text{W}$
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Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

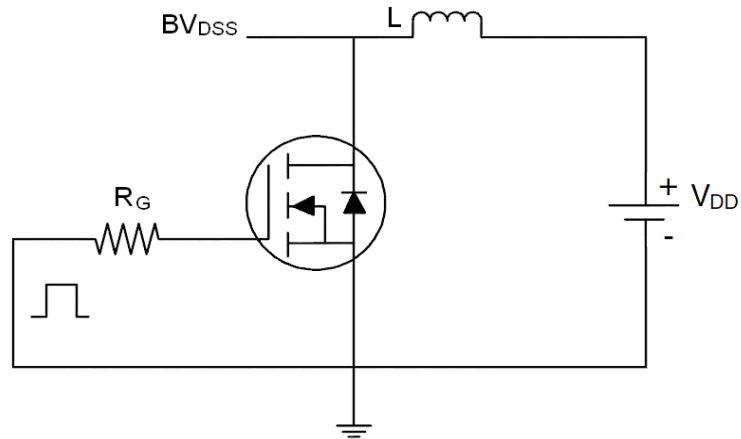
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	110	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.2	1.8	2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$	-	56	70	m Ω
		$V_{GS}=4.5V, I_D=3A$	-	65	85	
Gate resistance	R_G		-	0.6	-	Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	12	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=25V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1350	-	PF
Output Capacitance	C_{oss}		-	240	-	PF
Reverse Transfer Capacitance	C_{rss}		-	180	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, R_L=15\Omega, V_{GS}=10V, R_G=2.5\Omega$	-	13.8	-	nS
Turn-on Rise Time	t_r		-	9.3	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	43.8	-	nS
Turn-Off Fall Time	t_f		-	11.4	-	nS
Total Gate Charge	Q_g	$V_{DS}=50V, I_D=5A,$ $V_{GS}=10V$	-	30	-	nC
Gate-Source Charge	Q_{gs}		-	6.4	-	nC
Gate-Drain Charge	Q_{gd}		-	8.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=17A$	-	-	1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	17	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = 10A$ $di/dt = 100A/\mu s$ ^(Note 3)	-	54	-	nS
Reverse Recovery Charge	Q_{rr}		-	150	-	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

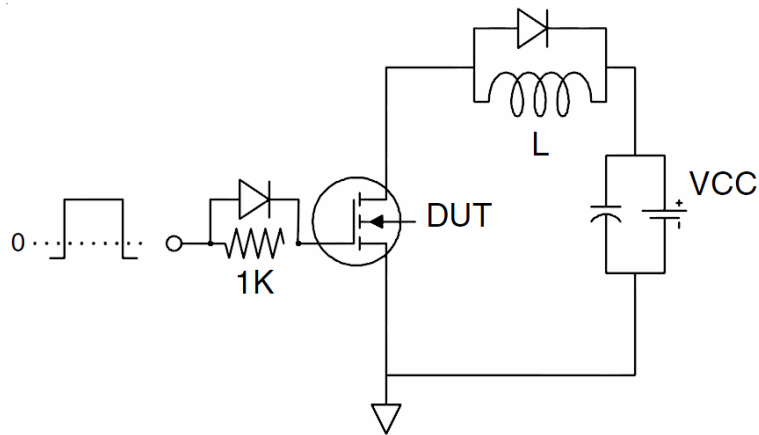
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_G=25\Omega$

Test Circuit

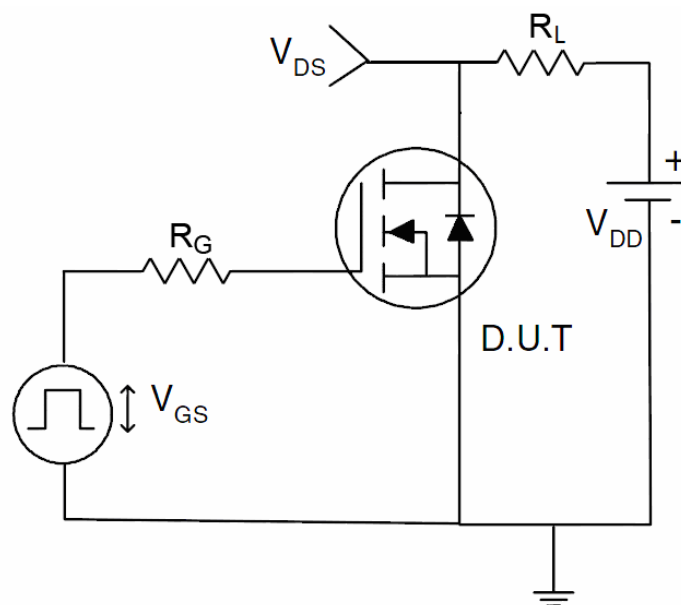
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

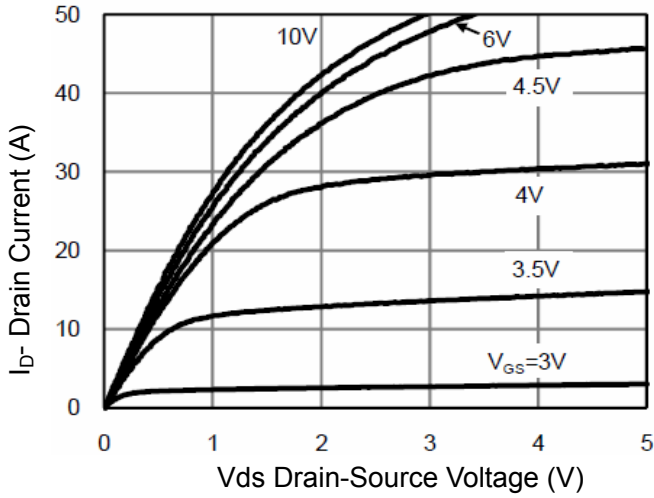


Figure 1 Output Characteristics

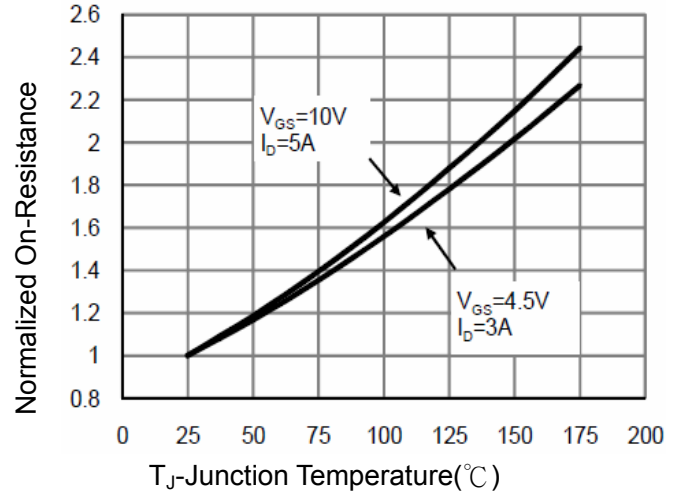


Figure 4 Rds(on)-Junction Temperature

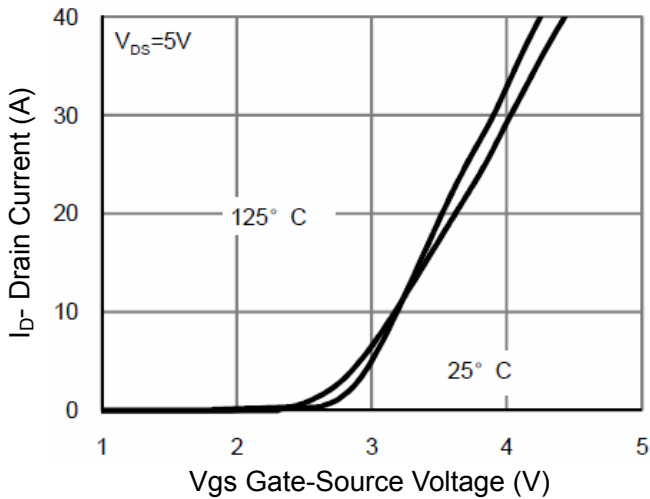


Figure 2 Transfer Characteristics

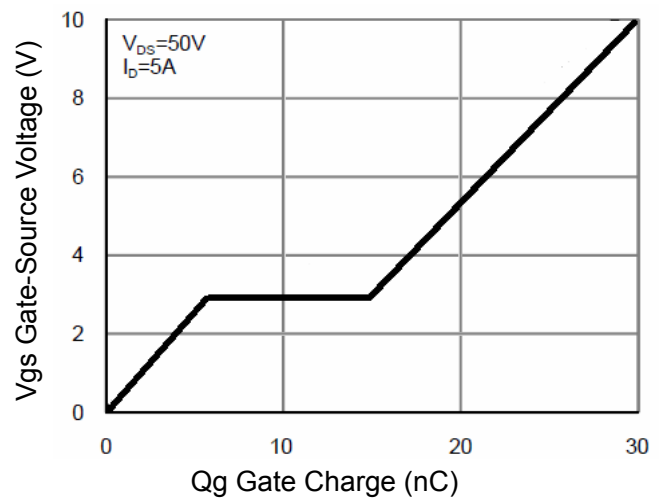


Figure 5 Gate Charge

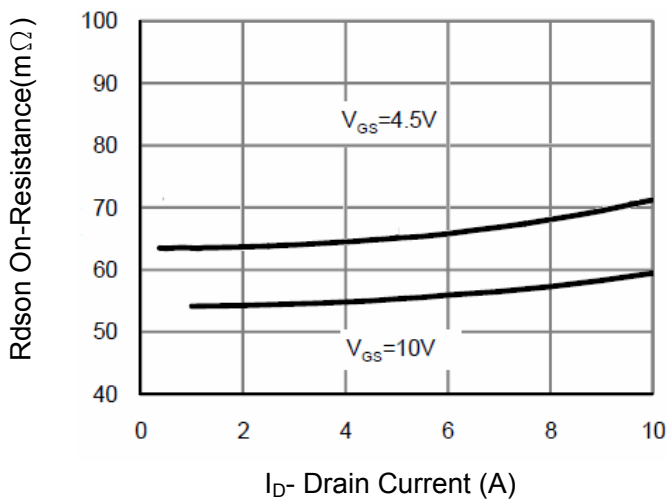


Figure 3 Rds(on)- Drain Current

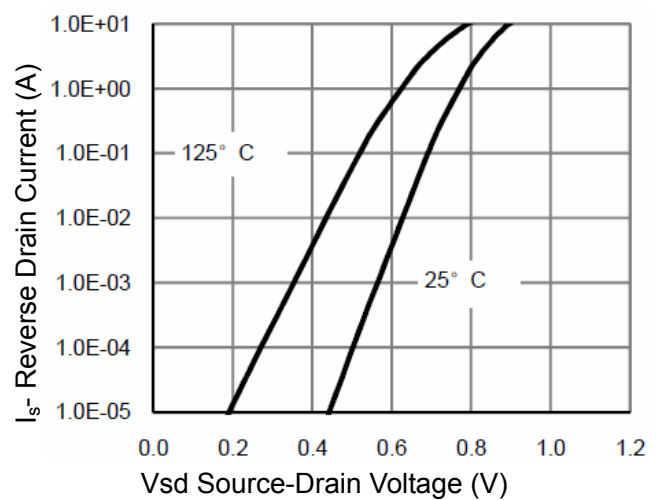


Figure 6 Source- Drain Diode Forward

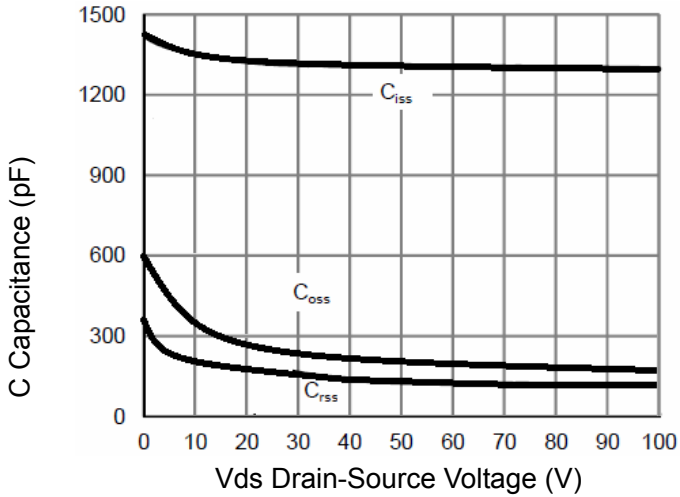


Figure 7 Capacitance vs Vds

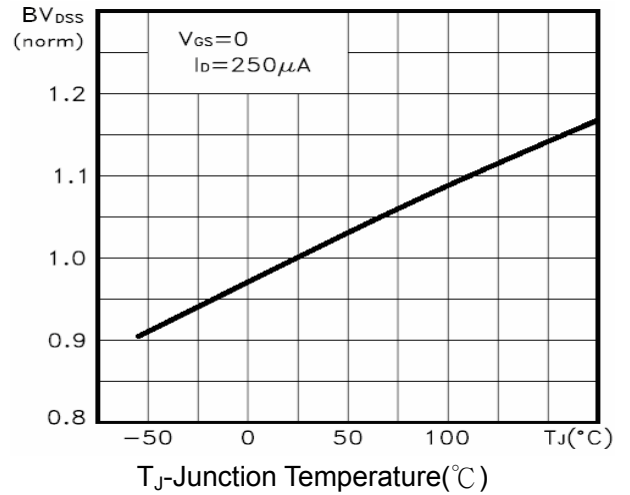


Figure 9 BV_{DSS} vs Junction Temperature

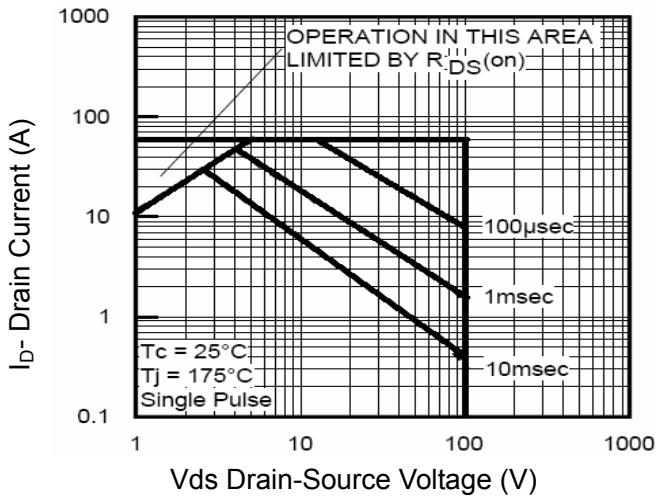


Figure 8 Safe Operation Area

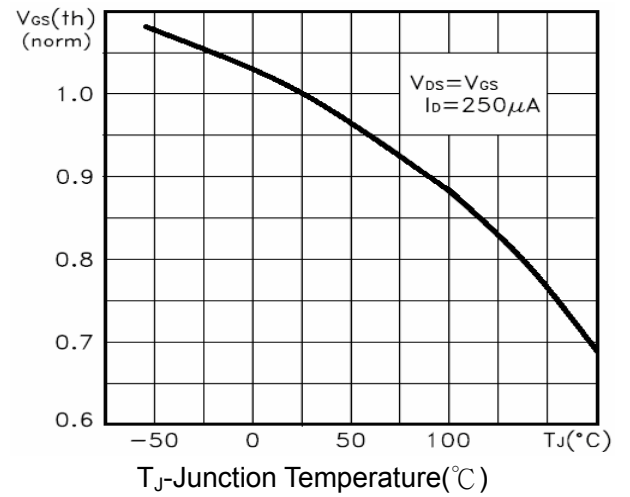


Figure 10 $V_{GS(th)}$ vs Junction Temperature

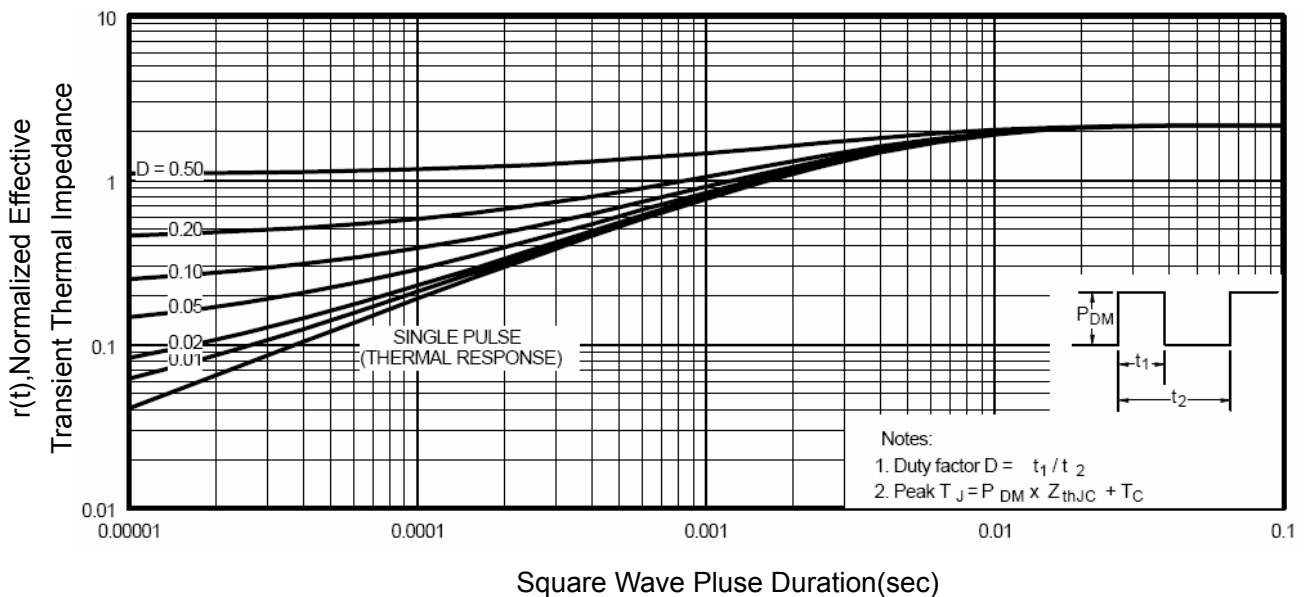
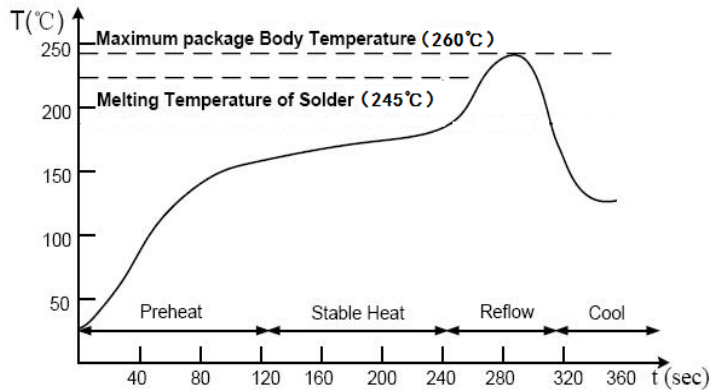


Figure 11 Normalized Maximum Transient Thermal Impedance

Suggested Soldering Temperature Profile



Note

- Recommended reflow methods: IR, vapor phase oven, hot air oven, wave solder.
- The device can be exposed to a maximum temperature of 260°C for 10 seconds.
- Devices can be cleaned using standard industry methods and solvents.
- If reflow temperatures exceed the recommended profile, devices may not meet the performance requirements.

Package Information

Tube Package

Package	Tube (mm)	Q'TY/Tube (Kpcs)	Box Size (mm)	QTY/Box (Kpcs)	Carton Size (mm)	Q'TY/Carton (Kpcs)
TO	525*31.9*6.4	0.05	545*150*45	1.0	575*245*170	5.0